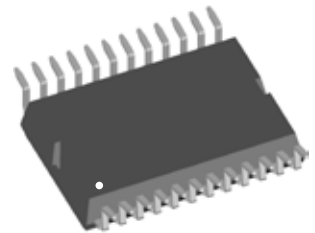
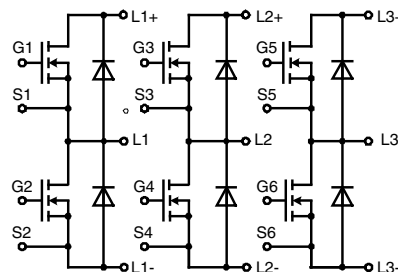


Three phase full Bridge

with Trench MOSFETs
in DCB isolated high current package

$V_{DSS} = 75 \text{ V}$
 $I_{D25} = 110 \text{ A}$
 $R_{DSon \text{ typ.}} = 4.0 \text{ m}\Omega$



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	75	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	110	A
I_{D90}	$T_C = 90^\circ\text{C}$	85	A
I_{F25}	$T_C = 25^\circ\text{C (diode)}$	110	A
I_{F90}	$T_C = 90^\circ\text{C (diode)}$	80	A

Applications

AC drives

- in automobiles
 - electric power steering
 - starter generator
- in industrial vehicles
 - propulsion drives
 - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Symbol	Conditions	Characteristic Values			
		$(T_{VJ} = 25^\circ\text{C, unless otherwise specified})$			
		min.	typ.	max.	
$R_{DSon}^{1)}$	on chip level at $V_{GS} = 10 \text{ V}$		4.0	4.9	$\text{m}\Omega$
			7.2	8.4	$\text{m}\Omega$
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}; I_D = 1 \text{ mA}$	2.0		4.0	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$		50	1	μA
					μA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2	μA
Q_g	$V_{GS} = 10 \text{ V}; V_{DS} = 36 \text{ V}; I_D = 25 \text{ A}$		115		nC
Q_{gs}			30		nC
Q_{gd}			30		nC
$t_{d(on)}$	inductive load $V_{GS} = 10 \text{ V}; V_{DS} = 30 \text{ V}$ $I_D = 80 \text{ A}; R_G = 39 \Omega;$ $T_J = 125^\circ\text{C}$		130		ns
t_r			100		ns
$t_{d(off)}$			500		ns
t_f			100		ns
E_{on}			0.20		mJ
E_{off}		0.50		mJ	
E_{recoff}		0.01		mJ	
R_{thJC}			1.0		K/W
R_{thJH}	with heat transfer paste (IXYS test setup)		1.3	1.6	K/W

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin \text{ to chip}})$

Source-Drain Diode

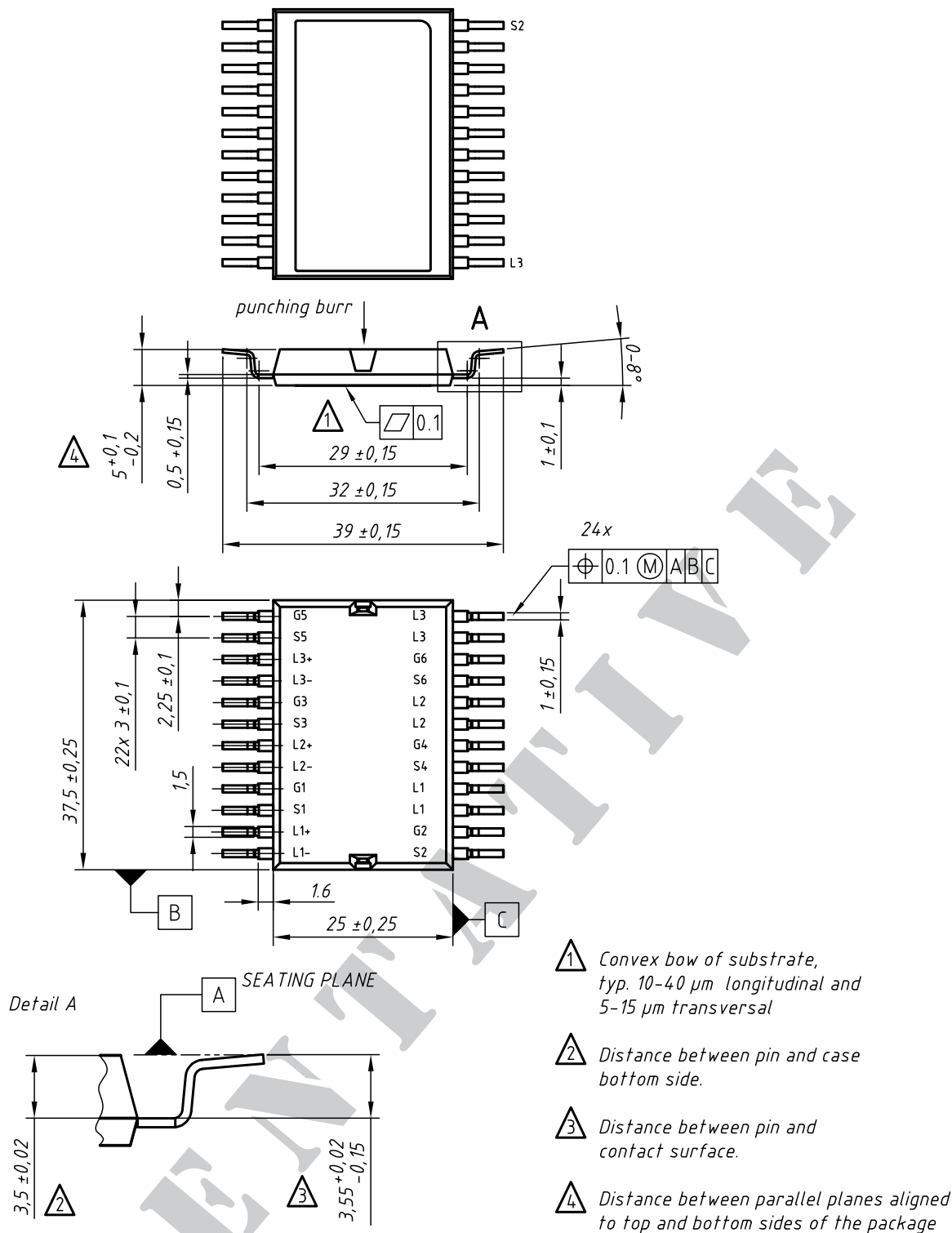
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
($T_J = 25^\circ\text{C}$, unless otherwise specified)					
V_{SD}	(diode) $I_F = 80\text{ A}$; $V_{GS} = 0\text{ V}$		0.9	1.2	V
t_{rr}	} $I_F = 80\text{ A}$; $-di_F/dt = 800\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$		55		ns
Q_{RM}			0.9		μC
I_{RM}			30		A

Component

Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections 2 pins for output L1, L2, L3	75	A
T_J		-55...+175	$^\circ\text{C}$
T_{stg}		-55...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}$, 50/60 Hz, $f = 1\text{ minute}$	1000	V~
F_C	mounting force with clip	50 - 250	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin\ to\ chip}^{1)}$			tbd	$\text{m}\Omega$
C_P	coupling capacity between shorted pins and back side metallization		160	pF
Weight			25	g

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin\ to\ Chip})$



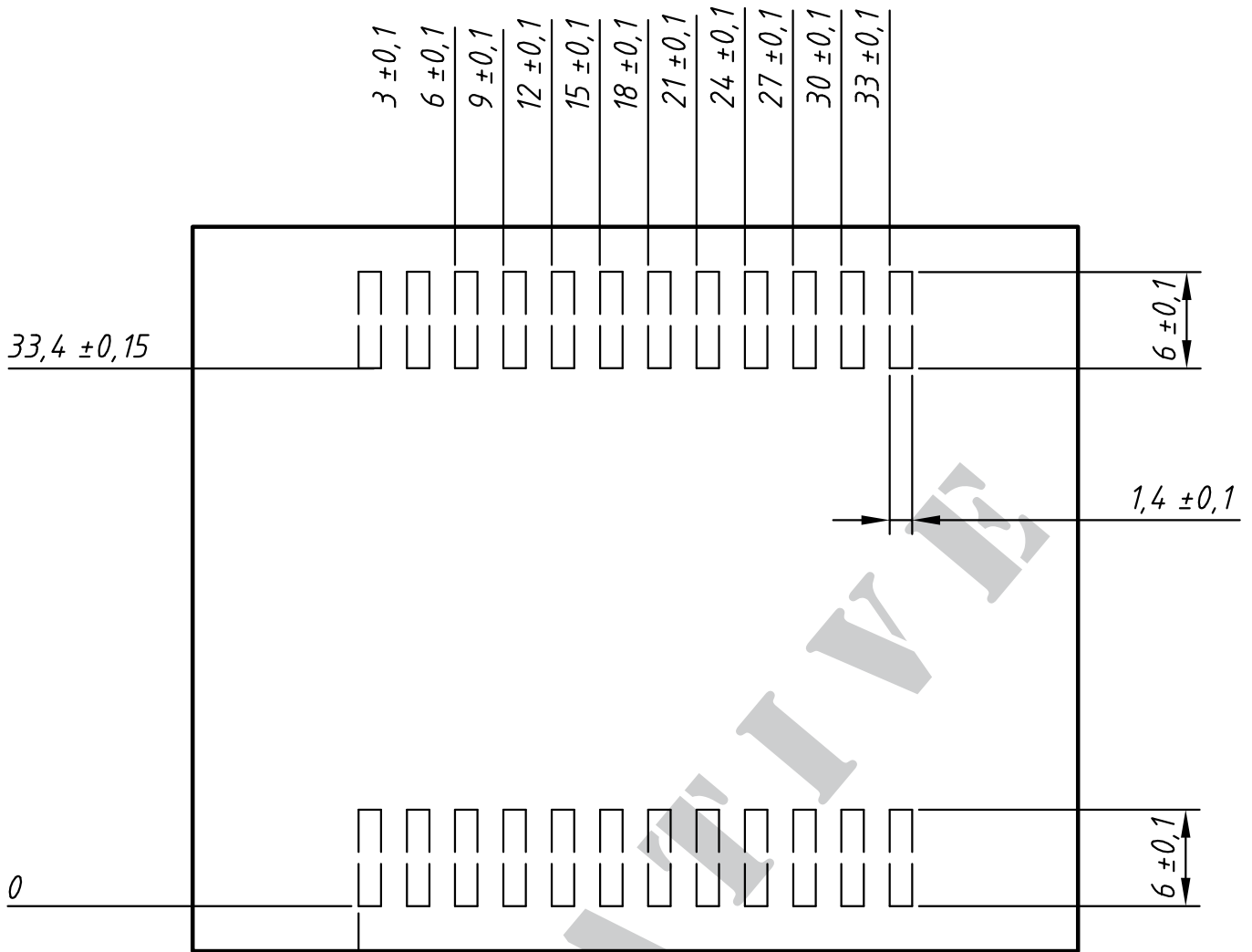
contact pin:

- galv. tin plating, per pin side: Sn 10...25 μ m, undercoating Ni 0,2...1 μ m
- stamping edges may be free of tin
- punching burr: $\leq 0,05$ mm

Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
SMD	Standard	GMM 3x120-0075X2 - SMD	GMM 3x120-0075X2	Blister	28	507 508

IXYS reserves the right to change limits, test conditions and dimensions.

20110307



Remarks:

- 1) pin layout / dimensions are conditionally
- 2) soldering paste thickness: 200µm